

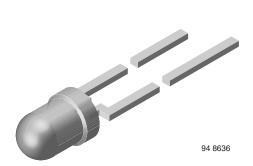
## **TSUS4400**

HALOGEN **FREE** 

**GREEN** 

# Vishay Semiconductors

# Infrared Emitting Diode, 950 nm, GaAs



www.vishay.com

### **DESCRIPTION**

TSUS4400 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue tinted plastic package.

### **FEATURES**

 Package type: leaded • Package form: T-1

Dimensions (in mm): Ø 3

• Peak wavelength:  $\lambda_p = 950 \text{ nm}$ 

High reliability

• Angle of half intensity:  $\varphi = \pm 18^{\circ}$ 

Low forward voltage

Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



- · Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- · Emitter in reflective sensors

PRODUCT SUMMARY				
COMPONENT	I <sub>e</sub> (mW/sr)	φ <b>(°)</b>	$\lambda_{\mathbf{p}}$ (nm)	t <sub>r</sub> (ns)
TSUS4400	15	± 18	950	800

### Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS4400	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

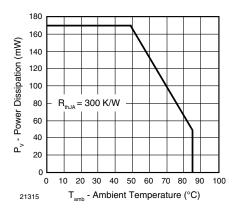
· MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5$ , $t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	2	Α	
Power dissipation		P <sub>V</sub>	170	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	-40 to + 85	°C	
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C	
Soldering temperature	t ≤ 5 s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction to ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	300	K/W	



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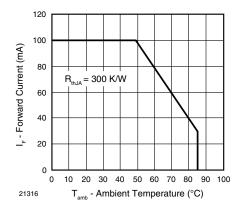


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

Fig. 2 - Forward Current Limit vs. Ambient Temperature

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>	-	1.3	1.7	V
	$I_F = 1.5 \text{ A}, t_p = 100 \mu \text{s}$	V <sub>F</sub>	-	2.2	-	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	TK <sub>VF</sub>	-	-1.3	-	mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>	=		100	μΑ
Breakdown voltage	I <sub>R</sub> = 100 μA	V <sub>(BR)</sub>	5	40	-	μΑ
Junction capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	Cj	-	30	-	pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	I <sub>e</sub>	7	15	35	mW/sr
	$I_F = 1.5 \text{ A}, t_p = 100 \mu \text{s}$	I <sub>e</sub>	-	140	-	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фe	-	20	-	mW
Temperature coefficient of $\phi_e$	I <sub>F</sub> = 20 mA	TKφ <sub>e</sub>	=	-0.8	-	%/K
Angle of half intensity		φ	=	± 18	-	0
Peak wavelength	I <sub>F</sub> = 100 mA	$\lambda_{p}$	-	950	-	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ	=	50	-	nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>	=	0.2	-	nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>	-	800	-	ns
	I <sub>F</sub> = 1.5 A	t <sub>r</sub>	-	400	-	ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>	-	800	-	ns
	I <sub>F</sub> = 1.5 A	t <sub>f</sub>	-	400	-	ns
Virtual source diameter		d	-	2.1	-	mm

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## **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

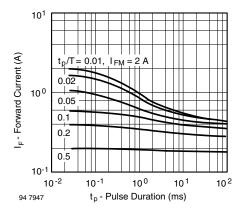


Fig. 3 - Pulse Forward Current vs. Pulse Duration

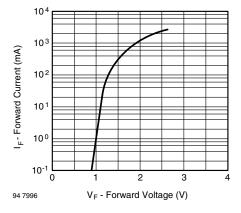


Fig. 4 - Forward Current vs. Forward Voltage

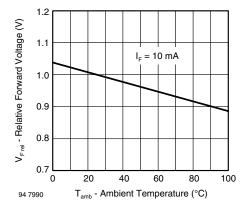


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

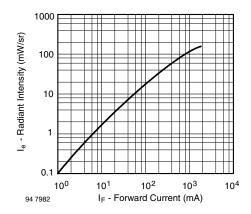


Fig. 6 - Radiant Intensity vs. Forward Current

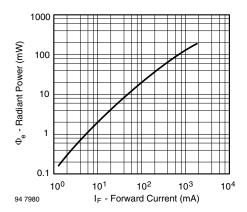


Fig. 7 - Radiant Power vs. Forward Current

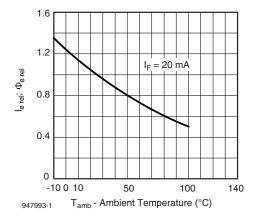


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature



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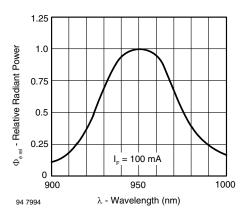


Fig. 9 - Relative Radiant Power vs. Wavelength

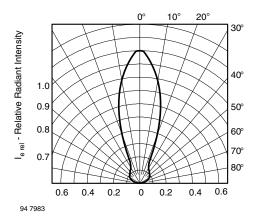
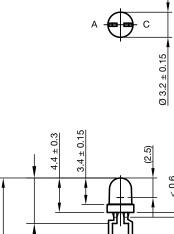
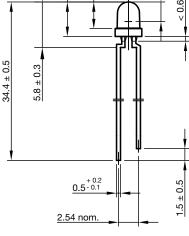


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

### **PACKAGE DIMENSIONS** in millimeters





technical drawings according to DIN specifications

Drawing-No.: 6.544-5255.01-4

Issue: 9; 28.07.14



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